

In the Specification:

Please amend paragraph 42 as follows:

FIG. 1 illustrates a flowchart describing an algorithm for determining and correcting a critical dimension (CD) error(s) for a feature(s) within a photoresist layer, wherein said feature(s) is to be subsequently transferred to a semiconductor substrate during a photolithography process, in accordance with embodiments of the present invention. Thus, a feature(s) will ultimately define a corresponding structure within the semiconductor substrate. The term “critical dimension error” (CD error) is defined herein as an incorrect dimension for the feature(s). The CD error may be caused during a photolithography process by, *inter alia*, an incorrect pattern or image within a mask, an error during a pattern transfer from the mask to the photoresist, an incorrect original design, etc. The CD error(s) is corrected during a semiconductor device manufacturing process at a photoresist level without building a new mask. Although the following description is described with reference to photolithography using radiation (e.g., laser 6A and 6B) and a mask, note that any lithography method known to a person of ordinary skill in the art may be used including, *inter alia*, a maskless lithography method, a direct write lithography method, etc. During ~~the~~ during a photolithography process (i.e., using radiation), a photomask (see mask 9 in FIG. 2A) is used to produce a plurality of features (e.g., feature 15B in FIG. 2B) within a semiconductor wafer (see semiconductor wafer 19 in FIG. 2B). Radiation is provided through the mask to project a patterned image on a photoresist layer that will define the plurality of features within the photoresist layer that remains after a subsequent process (e.g., chemical etch) that removes soluble portions of the photoresist layer. In turn, the plurality of features in the photoresist layer are utilized to define a plurality of structures, *inter alia*, doping

regions, deposition regions, etching regions, isolation regions, transistor gates, and other device structures and elements (e.g., electrical components) within the semiconductor substrate.

Additionally, the plurality of features in the photoresist layer may also define conductive lines or conductive pads associated with metal layers within the semiconductor substrate. During the above described process, the CD error(s) for the feature(s) within the layer of photoresist material on the semiconductor substrate may be caused by, *inter alia*, an incorrect pattern or image on a mask, an error during a pattern transfer from the mask to the photoresist, lens aberration during the image projection, an incorrect original design, etc. The CD error is corrected at a photoresist layer level as described below by FIG. 1.